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An Isolable Silanoic Ester by Oxygenation of a Stable Silylene

Shenglai Yao, Yun Xiong, Markus Brym, and Matthias Driess*

Institute of Chemistry: Metalorganics and Inorganic Materials Technische Universität Berlin, Strasse des 17. Juni

135, Sekr. C2, D-10623 Berlin, Germany

Received April 6, 2007; E-mail: matthias.driess@tu-berlin.de

The chemistry of stable main-group element compounds with silicon-heteroatom double bonds has witnessed tremendous progress over the past 25 years. This is evident by the fact that Si=X compounds (X = group 13 to 16 elements) possess a unique reactivity and thus serve as indispensable building blocks in both organosilicon chemistry and organic synthesis.¹ However, stable silicon homologues of ubiquitous ketones (R₂Si=O) and carboxylic acids (RSi(=O)OH) are still elusive. This is mainly due to the pronounced polarity of the Si=O double bond which accounts for the extraordinary high tendency of silanones to undergo oligomerization.² Additionally, silanoic acids (RSi(=O)OH; R = H, alkyl) tend to isomerize to their divalent silylene tautomers (RO-(OH)Si:).³ Therefore, silanones⁴ and silanoic acid derivatives⁵ are elusive species which have predominantly been investigated in cryogenic argon matrices. Recently, we succeeded in the synthesis of an isolable silaformamide-borane complex, $LSi(H)=O \rightarrow BR_{3}$,⁶ by a borane-assisted addition of water to the corresponding stable silvlene.⁷ The concept of donor-acceptor stabilization of the Si= O double bond has now prompted us to challenge the discouraging attempts to synthesize an isolable silanoic ester. To synthesize a silanoic ester stable at room-temperature we probed the suitability of the N \rightarrow Si donor supported siloxysilylene 1⁶ as possible precursor for gentle monooxygenation at the divalent silicon atom. In line with that, we also examined the dioxygenation of 1 with dioxygen which led to an unexpected new type of strained cyclodisiloxane. Here, we describe the first silanoic silvlester 2 and the striking cyclodisiloxane 4 which resulted from convenient oxygenation of the siloxysilylene $HSi(L')-O-(L)Si:1 \{L = HC[CMeN(aryl)]_2;$ L' = [L-H]; aryl = 2,6-diisopropylphenyl} with N₂O, CO₂, and O₂, respectively (Schemes 1 and 2). Exposure of a brown solution of the siloxysilylene 1 in toluene to N_2O at -78 °C leads to a gradual decoloration. Crystallization from the solution at -20 °C furnishes colorless plates of the desired silanoic silylester 2 in 79% yield. Remarkably, employing CO₂ as a cheaper monooxygen source leads to the same result.

Crystals of 2 are soluble in hydrocarbons and ethereal solvents. They are stable in dry-air and remain unchanged up to 200 °C in an anaerobic atmosphere. The composition of 2 is supported by multinuclear NMR, IR spectroscopy, correct combustion analysis, and EI-MS (M = 924 au). Its ¹H NMR spectrum exhibits two sets of the expected proton types and, thus, proves the presence of two rotational isomers, similar to the situation observed for the starting material 1.6 In addition, the ²⁹Si NMR spectrum shows two sets of resonances for the two chemically inequivalent ²⁹Si nuclei at $\delta =$ -55.0, -55.5 ppm (each a doublet, siloxy group, ¹J Si,H = 281 Hz) and -85.1, -85.8 ppm (each a singlet, LSi(=O)), respectively. As expected, the ²⁹Si chemical shift of the siloxy group in 2 is only marginally different from the respective values of the isomeric mixture of 1 ($\delta = -53.7, -54.2$ ppm). Remarkably, the ²⁹Si nucleus in the LSi=O moiety is even higher-field shifted than that in the silaformamide-borane complex LSi(H)=O \rightarrow B(C₆F₅)₃ (δ = -61.5

Scheme 1. Synthesis of the Silanoic Silylester 2 by Oxygenation of 1 and Formation of the MeOH Adduct 3







ppm). This indicates substantial Si=O π -bonding interaction in spite of the presence of tetracoordinate silicon and, thus, proves similar electronic features as present in the related silaformamide-borane complex.⁶ Apparently, the favorable Si=O π -bonding interaction through the oxygen lone-pair $n_{\pi} \rightarrow Si-N \sigma^*_{\pi}$ population (σ^*_{π} acceptor orbitals mainly located at silicon) is more effective than that in the aforementioned silaformamide complex. The latter possesses a Si-O bond order of ca. 1.8 based on its Si=O stretching vibration/force constant in comparison to the reference system H2-Si=O with a bond order set to 2.0. Unfortunately, the Si=O stretching vibration mode in 2 could not be unequivocally identified because of superimposition of signals in the characteristic region of the IR and Raman spectrum (1000-1200 cm⁻¹), respectively. However, in line with the presence of a Si=O double bond, 2 reacts with methanol to give the corresponding Si(OMe)-OH adduct 3 in almost quantitative yield (Scheme 1).

The latter has been characterized by multinuclear NMR spectroscopy and EI-MS (M = 956 au). The molecular structure of **2** has been confirmed by a single-crystal X-ray diffraction analysis (Figure 1). The two almost planar six-membered C₃N₂Si rings in **2** prefer a gauche-conformation and are linked by the O2 atom. The structure is most notable for its silanoic silylester array Si1(=O1)– O2–Si2 with the remarkably short Si1–O1 distance of 157.9(3) pm, which is a little longer than that in the related silaformamide complex LSi(H)=O→B(C₆F₅)₃ (155.2(2) pm). Likewise, the relatively short Si1=O1 distance in **2** can also be explained by the contribution of resonance betaine structures as previously suggested for related systems.^{6,8} Expectedly, the Si1–O2 (162.9(2) pm) and Si2–O2 bond lengths (162.6(2) pm) represent typical Si–O single bond values in siloxanes which are slightly shorter than those



Figure 1. Molecular structure of *2.* Thermal ellipsoids (C1–C5, C30–C34, N1–N4, O1, O2, Si1, Si2) are drawn at 50% probability level. H atoms (except those at C30) are omitted for clarity. Selected distances (pm): Si1–O1 157.9(3), Si1–O2 162.9(2), Si2–O2 162.6(2), Si1–N1 176.8(2), Si1–N2 178.3(2), Si2–N3 173.5(2), Si2–N4 174.6(2), N1–C2 137.1(3), N2–C4 136.3(3), N3–C31 140.3(3), N4–C33 139.9(3), C1–C2 147.4(3), C2–C3 138.4(4), C3–C4 139.6(3), C4–C5 147.6(3), C30–C31 142.4(4), C31–C32 139.2(4), C32–C33 139.5(4), C33–C34 145.7(3).



Figure 2. Molecular structure of **4.** Thermal ellipsoids (C1–C5, C30–C34, N1–N4, O1–O3, Si1, Si2) are drawn at 50% probability level. H atoms (except those at O1 and C30) are omitted for clarity. Selected interatomic distances (pm) and angles (deg): Si1–O1 163.3(3), Si1–O2 174.0(3), Si1–O3 174.5(3), Si1–N2 185.9(4), Si1–N1 189.6(4), Si2–O2 162.5(3), Si2–O3 162.5(3), Si2–N4 170.2(4), Si2–N3 172.0(3), Si1–Si2 246.8(2); Si2–O2–Si1 94.3(2), Si2–O3–Si1 94.1(2).

observed in 1 (165.6(1) and 163.2(1) pm).⁶ In line with that, the Si1-O2-Si2 angle of 140.5(1)° is similar to values observed for disiloxanes. As expected, the C-C and N-C distances in the C₃N₂-Si rings as well as the excocyclic C-C bond lengths exhibit significant differences owing to the varying π -systems in the backbone of the two distinct chelate ligands, L and L'. It is noteworthy that the steric congestion of the β -diketiminato ligand L in 2 is sufficient of preventing dimerization of the Si=O moiety in solution at ambient temperature. Thus we examined whether the corresponding stable dioxasilirane (cyclosilaperoxide) 4' could be synthesized by dioxygenation of the divalent silicon atom in 2 with dry dioxygen. In fact, brownish solutions of the silylene 1 in toluene react readily with molecular oxygen at -78 °C to give clear yellow solutions of a sole product. However, the conversion furnishes solely the isomeric 2,4-dioxa-1,3-disiletane 4 which has been isolated in 76% yield (Scheme 2).

To our knowledge, compound 4 represents a unique type of cyclodisiloxane which results by a remarkably clean dioxygenation process of a stable silvlene with O₂. Although the mechanism is

still unknown, we assume the formation of **4'** and **4''** as reactive intermediates (Scheme 2) in accord with results from related experiments where transient silylenes and O₂ have been converted under gas-phase conditions⁹ and in cryogenic argon matrices below $-250 \, ^{\circ}\text{C.}^{5}$ The composition and constitution of **4** have been supported by EI-MS (M = 940 au), correct combustion analysis, IR, and NMR spectroscopy. According to an X-ray diffraction analysis, **4** consists of two almost planar six-membered C₃N₂Sirings which are perpendicular to each other and linked by two Si1– O–Si2 bridges (Figure 2). Additionally, the Si1 atom bears a terminal OH group which leads to a planar, four-membered Si₂O₂cycle with, at the same time, tetracoordinate and neutral pentacoordinate silicon centers.

Expectedly, the Si–O and the Si–N distances of the pentacoordinate Si1 atom are longer than those of the Si2 atom owing to the higher coordination number. Likewise, the Si1–Si2 distance of 246.8(2) pm is significantly larger than that in related organocyclodisiloxanes of the type (R_2SiO_2 .¹⁰

Supporting Information Available: Experimental details for the synthesis and spectroscopic data of **2**, **3**, and **4** (PDF) and crystallographic data for **2** and **4** (CIF), respectively. This material is available free of charge via the Internet at http://pubs.acs.org.

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